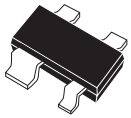
BAS28

DUAL, ISOLATED HIGH SPEED SWITCHING DIODE



SOT-143 CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR BAS28 type is a ultra-high speed silicon switching diode manufactured by the epitaxial planar process, in an epoxy molded surface mount package with isolated dual diodes, designed for high speed switching applications.

Marking code is A61.

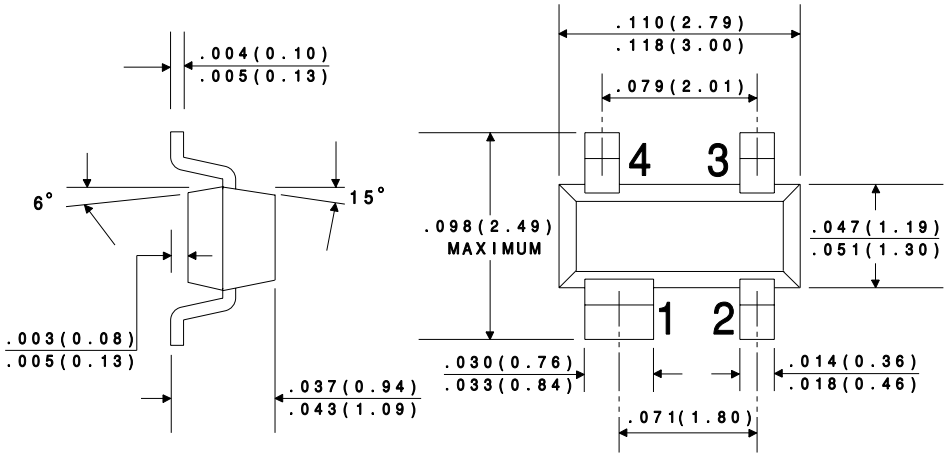
MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	75	V
Peak Repetitive Reverse Voltage	V_{RRM}	85	V
Continuous Forward Current	I_F	250	mA
Peak Repetitive Forward Current	I_{FRM}	250	mA
Forward Surge Current, tp=1 μsec.	I_{FSM}	4000	mA
Forward Surge Current, tp=1 msec.	I_{FSM}	2000	mA
Forward Surge Current, tp=1 sec.	I_{FSM}	1000	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	V_R=25V, T_A=150°C		30	μA
I_R	V_R=75V		1.0	μA
I_R	V_R=75V, T_A=150°C		50	μA
V_F	I_F=1.0mA		0.715	V
V_F	I_F=10mA		0.855	V
V_F	I_F=50mA		1.000	V
V_F	I_F=150mA		1.250	V
C_T	V_R=0, f=1 MHz		2.0	pF
t_{rr}	I_F=I_R=10mA, R_L=100Ω, Rec. to 1.0mA		6.0	ns
Q_S	I_F=10mA, V_R=5.0V, R_L=500Ω		45	pC
V_{FR}	I_F=10mA, t_r=20ns		1.75	V

All dimensions in inches (mm).



LEAD CODE:

1) CATHODE 1
2) CATHODE 2
3) ANODE 2
4) ANODE 1

R2